

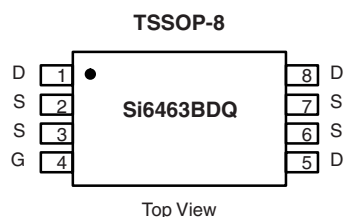
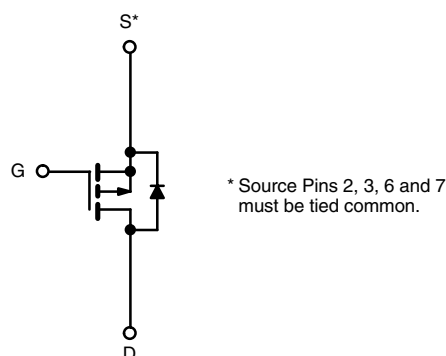
P-Channel 1.8-V (G-S) MOSFET

PRODUCT SUMMARY

V_{DS} (V)	$R_{DS(on)}$ (Ω)	I_D (A)
- 20	0.015 at $V_{GS} = - 4.5$ V	- 7.4
	0.020 at $V_{GS} = - 2.5$ V	- 6.3
	0.027 at $V_{GS} = - 1.8$ V	- 5.5

FEATURES

- Halogen-free
- TrenchFET® Power MOSFETs


RoHS
COMPLIANT

Ordering Information: Si6459BDQ-T1-GE3 (Lead (Pb)-free and Halogen-free)


P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS $T_A = 25$ °C, unless otherwise noted

Parameter		Symbol	10 s	Steady State	Unit
Drain-Source Voltage		V_{DS}	- 20		V
Gate-Source Voltage		V_{GS}	± 8		
Continuous Drain Current ($T_J = 150\text{ }^{\circ}\text{C}$) ^a	$T_A = 25\text{ }^{\circ}\text{C}$	I_D	- 7.4	- 6.2	A
	$T_A = 70\text{ }^{\circ}\text{C}$		- 5.9	- 4.9	
Pulsed Drain Current (10 μs Pulse Width)		I_{DM}	- 30		
Continuous Source Current (Diode Conduction) ^a		I_S	- 1.35	- 0.95	W
Maximum Power Dissipation ^a	$T_A = 25\text{ }^{\circ}\text{C}$	P_D	1.5	1.05	
	$T_A = 70\text{ }^{\circ}\text{C}$		1.0	0.67	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	- 55 to 150		$^{\circ}\text{C}$

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^a	R_{thJA}	65	83	°C/W
		100	120	
Maximum Junction-to-Foot	R_{thJF}	46	56	

Notes:

a. Surface Mounted on 1" x 1" FR4 board.

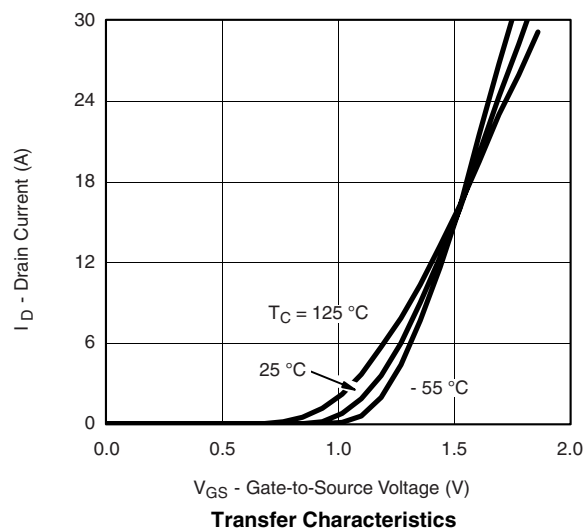
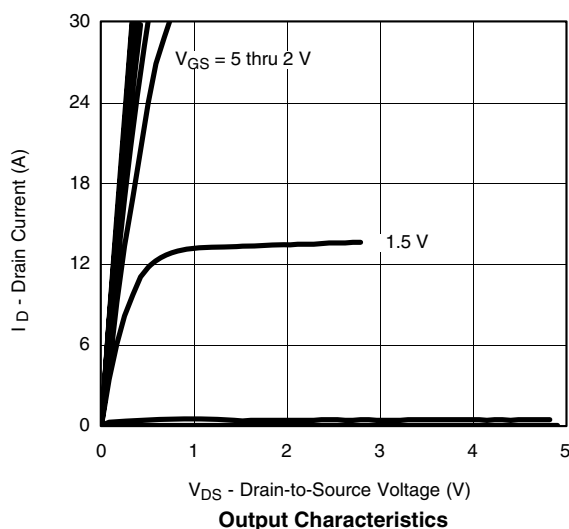
SPECIFICATIONS $T_J = 25^\circ\text{C}$, unless otherwise noted						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = -250\ \mu\text{A}$	-0.45		-0.8	V
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0\ \text{V}$, $V_{GS} = \pm 8\ \text{V}$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -20\ \text{V}$, $V_{GS} = 0\ \text{V}$			-1	μA
		$V_{DS} = -20\ \text{V}$, $V_{GS} = 0\ \text{V}$, $T_J = 70^\circ\text{C}$			-10	
On-State Drain Current ^a	$I_{D(on)}$	$V_{DS} = -5\ \text{V}$, $V_{GS} = -4.5\ \text{V}$	-20			A
Drain-Source On-State Resistance ^a	$R_{DS(on)}$	$V_{GS} = -4.5\ \text{V}$, $I_D = -7.4\ \text{A}$		0.011	0.015	Ω
		$V_{GS} = -2.5\ \text{V}$, $I_D = -6.3\ \text{A}$		0.015	0.020	
		$V_{GS} = -1.8\ \text{V}$, $I_D = -5.5\ \text{A}$		0.020	0.027	
Forward Transconductance ^a	g_{fs}	$V_{DS} = -15\ \text{V}$, $I_D = -7.4\ \text{A}$		34		S
Diode Forward Voltage ^a	V_{SD}	$I_S = -1.3\ \text{A}$, $V_{GS} = 0\ \text{V}$		-0.64	-1.1	V
Dynamic^b						
Total Gate Charge	Q_g	$V_{DS} = -10\ \text{V}$, $V_{GS} = -5\ \text{V}$, $I_D = -7.4\ \text{A}$		40	60	nC
Gate-Source Charge	Q_{gs}			5.2		
Gate-Drain Charge	Q_{gd}			8		
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = -10\ \text{V}$, $R_L = 15\ \Omega$ $I_D \cong -1\ \text{A}$, $V_{GEN} = -4.5\ \text{V}$, $R_G = 6\ \Omega$		35	55	ns
Rise Time	t_r			40	60	
Turn-Off Delay Time	$t_{d(off)}$			190	300	
Fall Time	t_f			90	150	
Source-Drain Reverse Recovery Time	t_{rr}	$I_F = -1.3\ \text{A}$, $di/dt = 100\ \text{A}/\mu\text{s}$		75	120	

Notes:

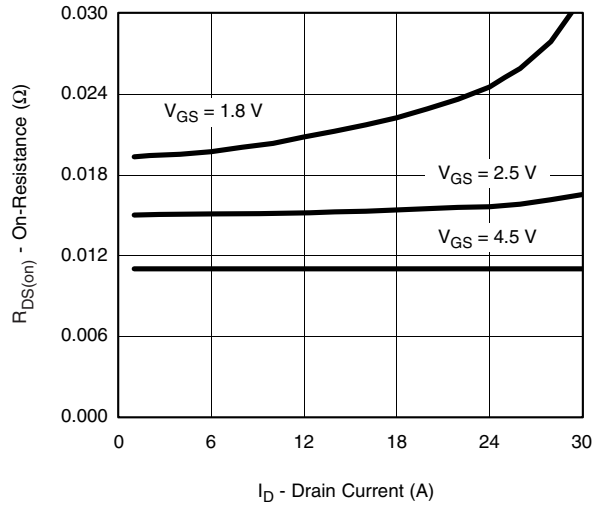
a. Pulse test; pulse width $\leq 300\ \mu\text{s}$, duty cycle $\leq 2\%$.

b. Guaranteed by design, not subject to production testing.

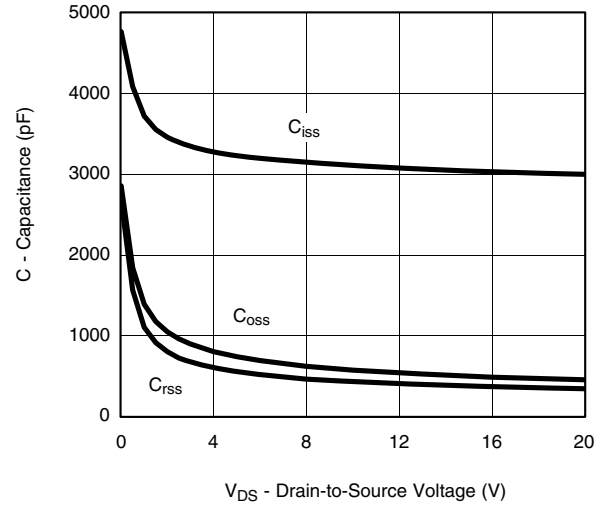
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS 25°C , unless otherwise noted

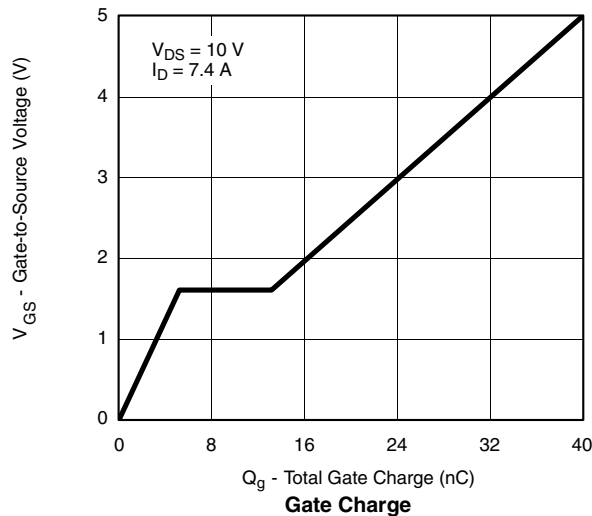
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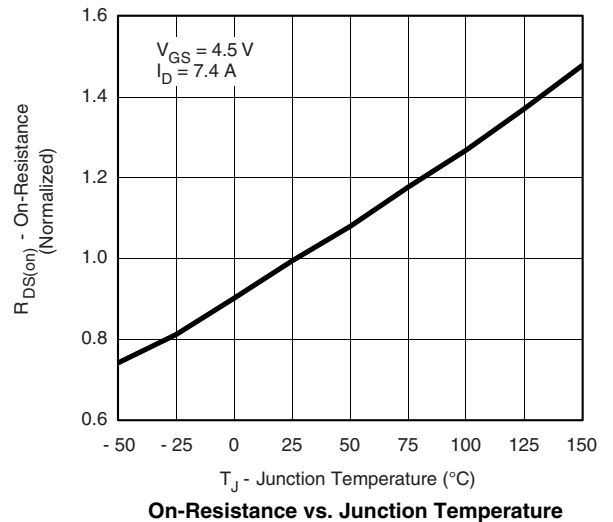
On-Resistance vs. Drain Current



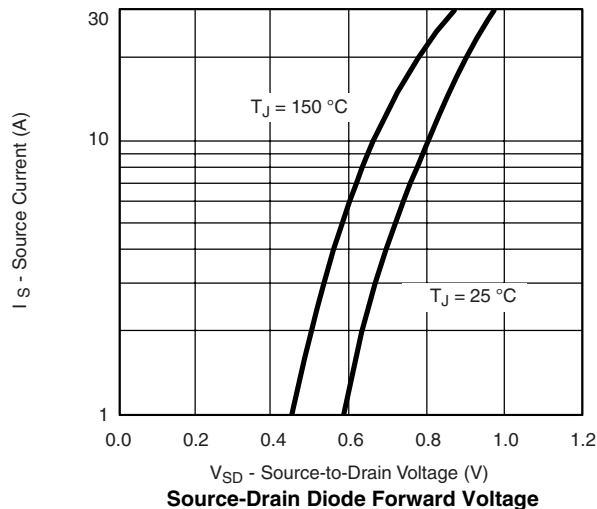
Capacitance



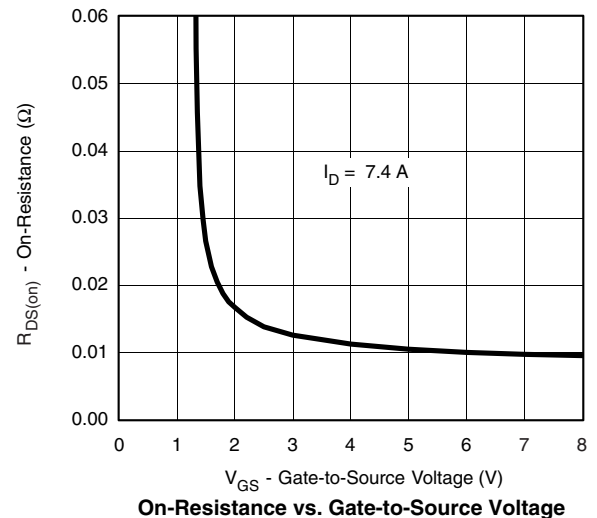
Gate Charge



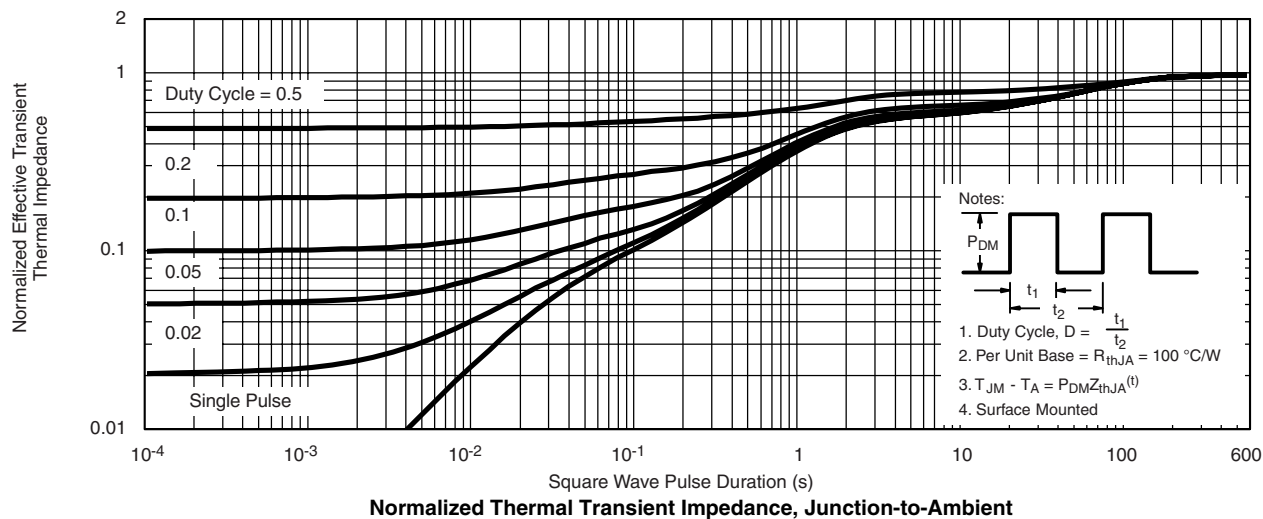
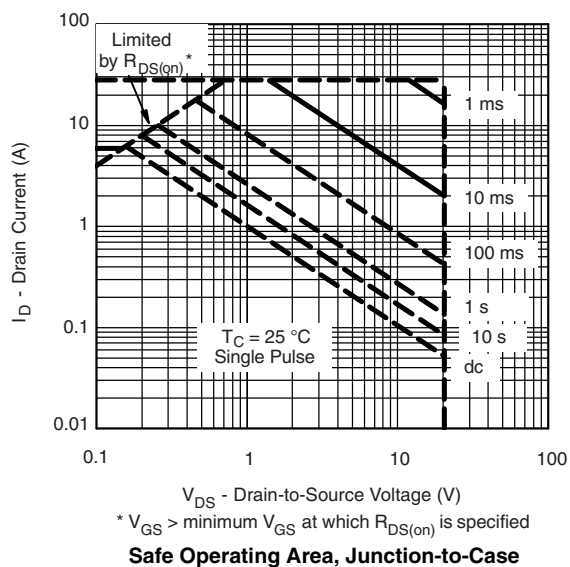
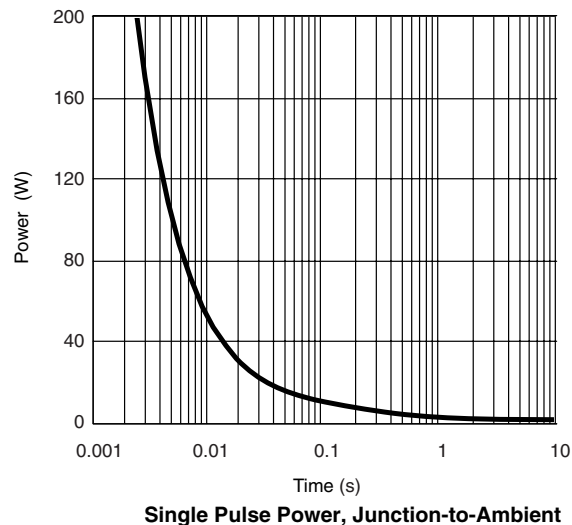
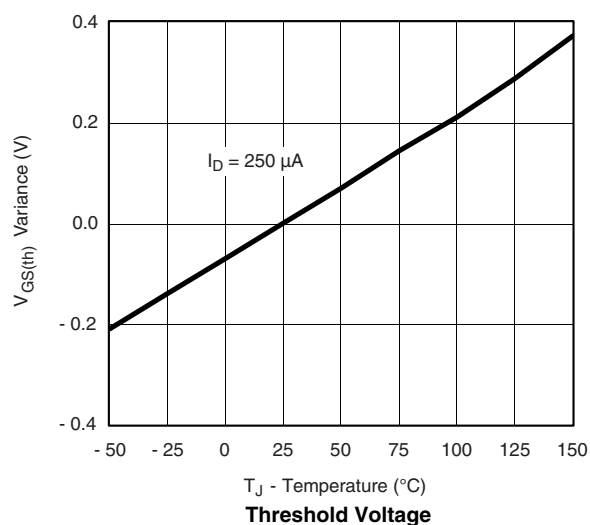
On-Resistance vs. Junction Temperature



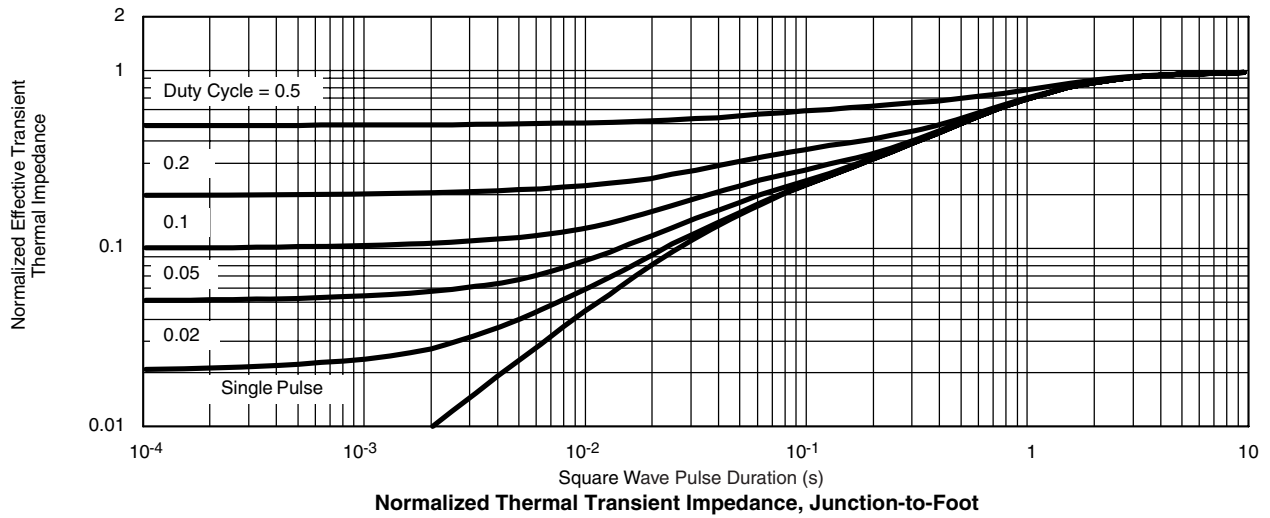
Source-Drain Diode Forward Voltage



On-Resistance vs. Gate-to-Source Voltage

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